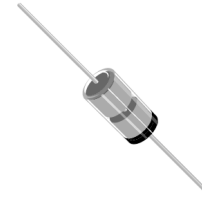


500mW Zener Diodes

Features

- 500mW Power Dissipation
- High Stability
- Zener Voltage from 2.7V to 43V
- High temperature soldering guaranteed 265°C/10 seconds
/.037" (9.5mm) lead length,
- RoHS compliant



DO-35



Mechanical Data

Case:	DO-35, Molded Glass
Terminals:	Axial leads, solderable per MIL-STD-202, Method 208
Weight:	0.125 gram

Maximum Ratings *(T_{Ambient}=25°C unless noted otherwise)*

Symbol	Description	Value	Unit	Conditions
PD	Power Dissipation TL=75°C	500	mW	
VF	Forward Voltage	1.5	V	IF= 0.1 A
TJ	Max. Junction Temperature	175	° C	
TSTG	Storage Temperature Range	-65 to +175	° C	

Electrical Characteristics ($T_{Ambient}=25^{\circ}C$ unless noted otherwise)

P/N	Normal Zener Voltage			Max Voltage Change	Max Zener Current	Max Reverse Current	
	VZ @ IZT=50 μ A			Δ VZ (V) note		IR @ VR	
	Nom. V	Min. V	Max. V		mA	μ A	VR
1N4678	1.8	1.710	1.890	0.70	120	7.5	1.0
1N4679	2.0	1.900	2.100	0.70	110	5.0	1.0
1N4680	2.2	2.090	2.310	0.75	100	4.0	1.0
1N4681	2.4	2.280	2.520	0.80	95.0	2.0	1.0
1N4682	2.7	2.565	2.835	0.85	90.0	1.0	1.0
1N4683	3.0	2.850	3.150	0.90	85.0	0.8	1.0
1N4684	3.3	3.135	3.465	0.95	80.0	7.5	1.5
1N4685	3.6	3.420	3.780	0.95	75.0	7.5	2.0
1N4686	3.9	3.705	4.095	0.97	70.0	5.0	2.0
1N4687	4.3	4.085	4.515	0.99	65.0	4.0	2.0
1N4688	4.7	4.465	4.935	0.99	60.0	10	3.0
1N4689	5.1	4.845	5.355	0.97	55.0	10	3.0
1N4690	5.6	5.320	5.880	0.96	50.0	10	4.0
1N4691	6.2	5.890	6.510	0.95	45.0	10	5.0
1N4692	6.8	6.460	7.140	0.90	35.0	10	5.1
1N4693	7.5	7.125	7.875	0.75	31.8	10	5.7
1N4694	8.2	7.790	8.610	0.50	29.0	1.0	6.2
1N4695	8.7	8.265	9.135	0.10	27.6	1.0	6.6
1N4696	9.1	8.645	9.555	0.08	26.2	1.0	6.9
1N4697	10	9.500	10.50	0.10	24.8	1.0	7.6
1N4698	11	10.45	11.55	0.11	21.6	0.05	8.4
1N4699	12	11.40	12.60	0.12	20.4	0.05	9.1
1N4700	13	12.35	13.65	0.13	19.0	0.05	9.8
1N4701	14	13.30	14.70	0.14	17.5	0.05	10.6
1N4702	15	14.25	15.75	0.15	16.3	0.05	11.4
1N4703	16	15.20	16.80	0.16	15.4	0.05	12.1
1N4704	17	16.15	17.85	0.17	14.5	0.05	12.9

P/N	Normal Zener Voltage			Max Voltage Change	Max Zener Current	Max Reverse Current	
	VZ @ IZT=50µA			ΔVZ (V) note		IR @ VR	
	Nom. V	Min. V	Max. V		mA	µA	VR
1N4705	18	17.10	18.90	0.18	13.2	0.05	13.6
1N4706	19	18.05	19.95	0.19	12.5	0.05	14.4
1N4707	20	19.00	21.00	0.20	11.9	0.01	15.2
1N4708	22	20.90	23.10	0.22	10.8	0.01	16.7
1N4709	24	22.80	25.20	0.24	9.9	0.01	18.2
1N4710	25	23.75	26.25	0.25	9.5	0.01	19.0
1N4711	27	25.65	28.35	0.27	8.8	0.01	20.4
1N4712	28	26.60	29.40	0.28	8.5	0.01	21.2
1N4713	30	28.50	31.50	0.30	7.9	0.01	22.8
1N4714	33	31.35	34.65	0.33	7.2	0.01	25.0
1N4715	36	34.20	37.80	0.36	6.6	0.01	27.3
1N4716	39	37.05	40.95	0.39	6.1	0.01	29.6
1N4717	43	40.85	45.15	0.43	5.5	0.01	32.6

Note. ΔVZ (V) is the difference between VZ at 100µA and at 10µA.

Typical Characteristics Curves

Fig.1- Total Power Dissipation vs. Ambient Temperature

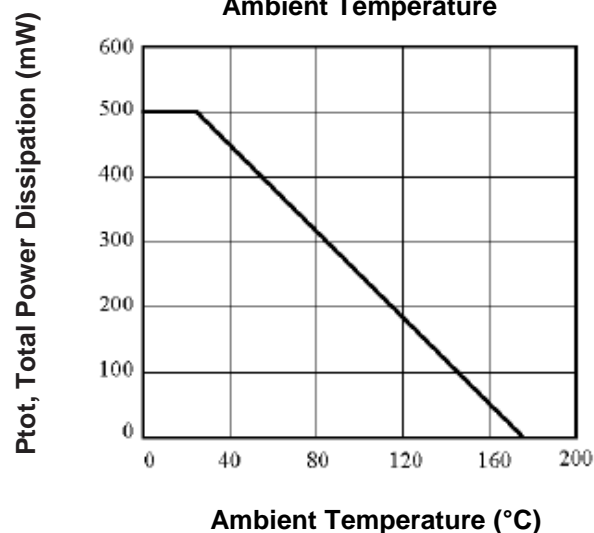


Fig.2- Z-Current vs. Z-Voltage

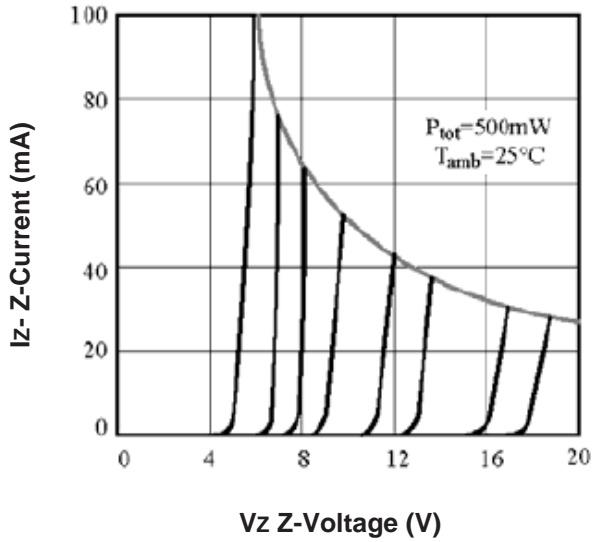


Fig.3- Z-Current vs. Z-Voltage

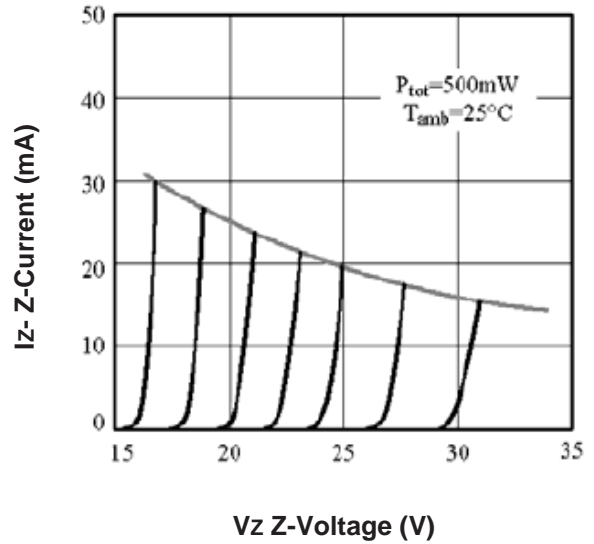


Fig.4- Forward Current vs. Forward Voltage

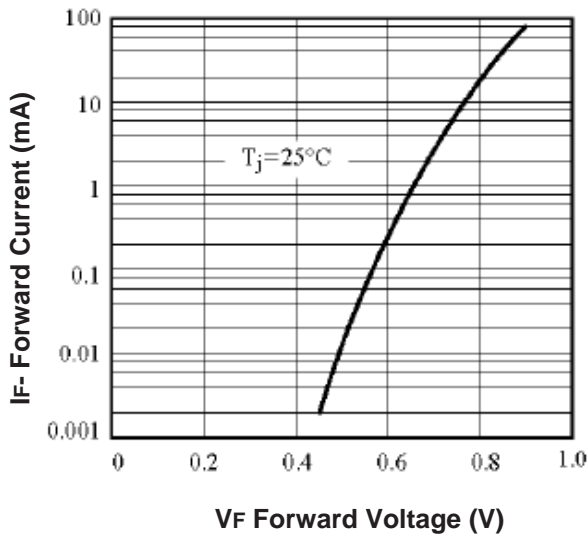
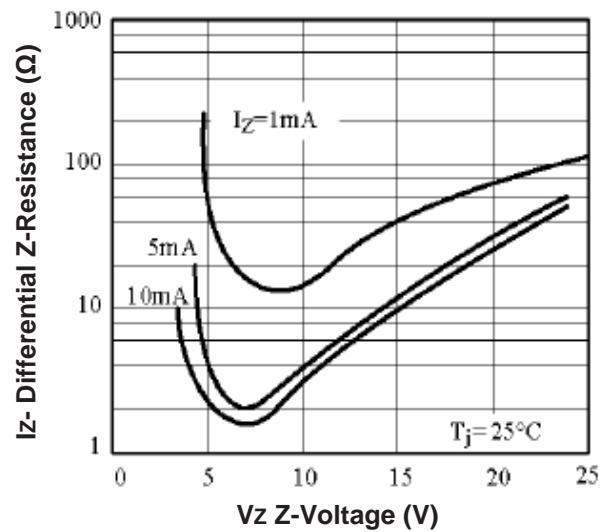
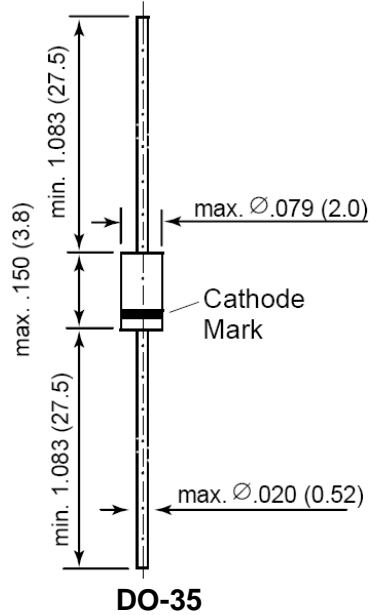


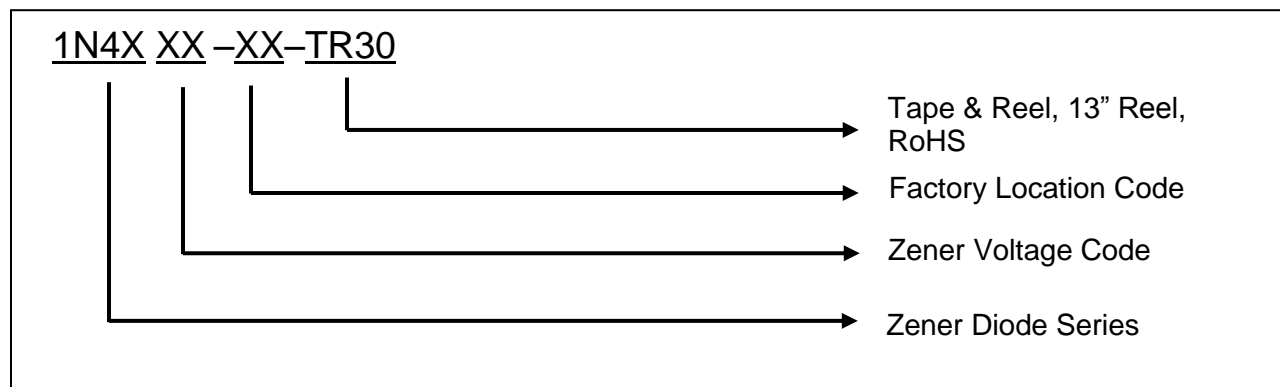
Fig.5- Differential Z-Resistance vs. Z-Voltage



Dimensions in inch (mm)



Ordering Information



How to contact us

US HEADQUARTERS

28040 WEST HARRISON PARKWAY, VALENCIA, CA 91355-4162

Tel: (800)-TAITRON (800)-824-8766 (661)-257-6060

Fax: (800)-TAITFAX (800)-824-8329 (661)-257-6415

Email: taitron@taitroncomponents.com

Http://www.taitroncomponents.com

TAITRON COMPONENTS MEXICO, S.A .DE C.V.

BOULEVARD CENTRAL 5000 INTERIOR 5 PARQUE INDUSTRIAL ATITALAQUIA, HIDALGO

C.P. 42970 MEXICO

Tel: +52-55-5560-1519

Fax: +52-55-5560-2190

TAITRON COMPONENTS INCORPORATED TAIWAN, TAIPEI

6F., No.190, Sec. 2, Zhongxing Rd., Xindian Dist., New Taipei City 23146, Taiwan R.O.C.

Tel: 886-2-2913-6238

Fax: 886-2-2913-6239

TAITRON COMPONETS INCORPORATED, SHANGHAI REPRESENTATIVE OFFICE

METROBANK PLAZA, 1160 WEST YAN'AN ROAD, SUITE 1503, SHANGHAI, 200052, CHINA

Tel: +86-21-5424-9942

Fax: +86-21-5424-9931